

# Accepted Manuscript

Self-rectifying resistive switching behavior observed in  $\text{Al}_2\text{O}_3$ -based resistive switching memory devices with  $p\text{-AlGaIn}$  semiconductor bottom electrode

Hee-Dong Kim, Sungho Kim, Min Ju Yun



PII: S0925-8388(18)30363-3

DOI: [10.1016/j.jallcom.2018.01.345](https://doi.org/10.1016/j.jallcom.2018.01.345)

Reference: JALCOM 44809

To appear in: *Journal of Alloys and Compounds*

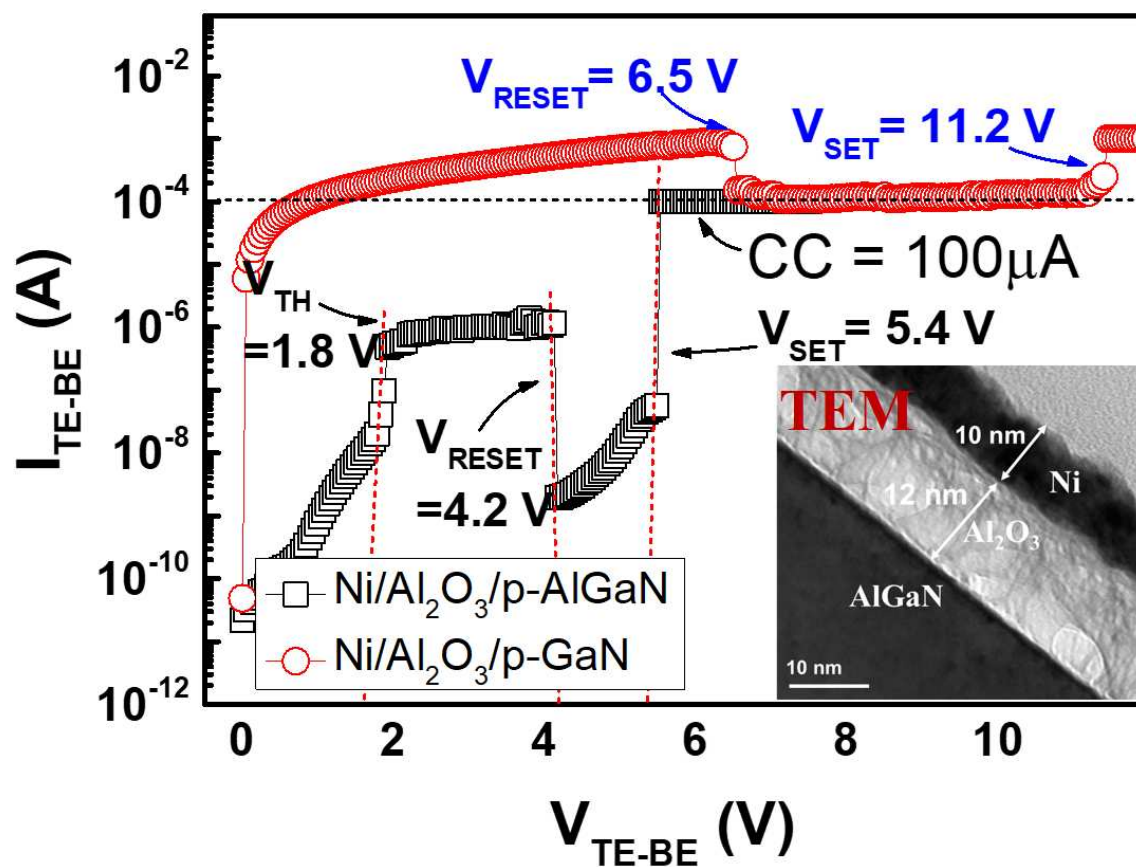
Received Date: 12 September 2017

Revised Date: 25 January 2018

Accepted Date: 27 January 2018

Please cite this article as: H.-D. Kim, S. Kim, M.J. Yun, Self-rectifying resistive switching behavior observed in  $\text{Al}_2\text{O}_3$ -based resistive switching memory devices with  $p\text{-AlGaIn}$  semiconductor bottom electrode, *Journal of Alloys and Compounds* (2018), doi: 10.1016/j.jallcom.2018.01.345.

This is a PDF file of an unedited manuscript that has been accepted for publication. As a service to our customers we are providing this early version of the manuscript. The manuscript will undergo copyediting, typesetting, and review of the resulting proof before it is published in its final form. Please note that during the production process errors may be discovered which could affect the content, and all legal disclaimers that apply to the journal pertain.



Download English Version:

<https://daneshyari.com/en/article/7993536>

Download Persian Version:

<https://daneshyari.com/article/7993536>

[Daneshyari.com](https://daneshyari.com)